

High speed series fifth generation

High speed 5 IGBT in TRENCHSTOP™ 5 technology copacked with full-rated RAPID 1 fast and soft antiparallel diode

Features and Benefits:

High speed H5 technology offering

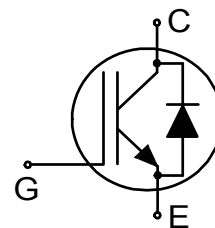
- Best-in-Class efficiency in hard switching and resonant topologies
- Plug and play replacement of previous generation IGBTs
- 650V breakdown voltage
- Low gate charge Q_G
- IGBT copacked with full-rated RAPID 1 fast and soft antiparallel diode
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Applications:

- Uninterruptible power supplies
- Solar converters
- Welding converters
- Mid to high range switching frequency converters

Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
IKW75N65EH5	650V	75A	1.65V	175°C	K75EEH5	PG-TO247-3

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